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		Application Number	10/797,188
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Confirmation Number	4959
		Filing Date	March 11, 2004
		First Named Inventor	Taiji EMA et al.
		Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	960045E
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US			
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
LTUE	1	JP	3-64964		03-20-1991	Toshiba Corp.	Abstract
LTUE	2	JP	3-174765		07-29-1991	OKI Electric Ind. Co. Ltd.	Abstract
LTUE	3	JP	3-174766		07-29-1991	Toshiba Corp.	Abstract
LTUE	4	JP	5-136369		06-01-1993	Sharp Corp.	Abstract
LTUE	5	JP	5-145036		06-11-1993	Toshiba Corp.	Abstract
LTUE	6	JP	5-218332		08-27-1993	Samsung Electron Co. Ltd.	Abstract
LTUE	7	JP	5-243517		09-21-1993	NEC Corp.	Abstract
LTUE	8	JP	5-304269		11-16-1993	NEC Corp.	Abstract
LTUE	9	JP	6-37272		02-10-1994	Toshiba Corp.	Abstract
LTUE	10	JP	6-37273		02-10-1994	Toshiba Corp.	Abstract
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LTUE	12	JP	6-120447		04-28-1994	Mitsubishi Electric Corp.	Abstract

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶

Examiner Signature	/Lynette Umez Eronini/ (07/06/2006)	Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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INFORMATION DISCLOSURE CITATION	Atty. Docket No. 960045E	Serial No. To be assigned
	Applicant(s): Taiji EMA et al.	
	Filing Date: Herewith	Group Art Unit: To be assigned

PTO-1449

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Examiner	Document No.	Name	Date	Class	Subclass	Filing Date
Initial	(If appropriate)					
<u>LTUE</u>	AB	5,502,336	Park et al.	03/96		
<u>LTUE</u>	AC	5,479,054	Tottori	12/95		
<u>LTUE</u>	AD	5,338,700	Dennison et al.	08/94		
<u>LTUE</u>	AE	4,974,040	Taguchi et al.	11/90		
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<u>LTUE</u>	AG	5,196,910	Moriuchi et al.	03/93		
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<u>LTUE</u>	AN	61-176148	08/07/96 Japan
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<u>LTUE</u>	AR	B.LUTHER et al.; Planar Copper-Polyimide Back End of the Line"; Proceedings of 10 th International VMIC; pages 15-21; June 1993.
<u>LTUE</u>	AS	B.M. SOMERO et al.; "A Modular in-situ Integration Scheme for Deep Submicron", Proceedings of 10 th International VMIC; pages 28-34; June 1993.
<u>LTUE</u>	AT	M.F. CHISHOLM et al.; "A High Performance 0.5 um Five-Level Metal Process with Extendibility of Sub-Half Micron"; pages 22-28; June 1994.
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<u>LTUE</u>	AV	I. NAIKI et al.; "Center Wordline Cell: A New Symmetric Layout Cell for 64Mb SRAM"; Technical Digest of IEDM; pages 817-820; December 1993.
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<u>LTUE</u>	AX	H.K. KANG et al.; "Highly Manufacturable Process Technology for Reliable 256 Mbit and 1 Gbit DRAMs"; Technical Digest of IEDM; pages 635-638; December 1994.
<u>LTUE</u>	A Y	Y. OHJI et al.; "Ta ₂ O ₅ Capacitors Dielectric Material for Giga-bit DRAMs"; Technical Digest of IEDM; pages 111-114; December 1995.
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<u>LTUE</u>	BC	
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